



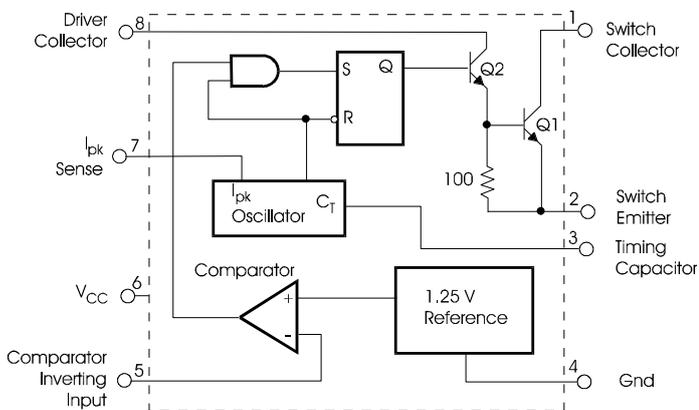
DESCRIPTION

The 34063M3K series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature-compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in step-down and step-up and voltage-inverting applications with a minimum number of external components.

FEATURES

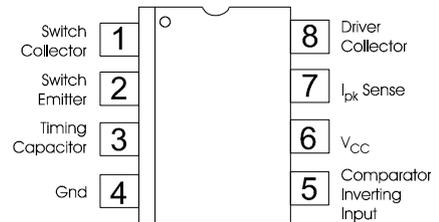
- Operation from 3.0 V to 40 V input
- Low standby current
- Current limiting
- Output switch current up to 1.5 A
- Adjustable output voltage
- Operation at frequencies up to 100 kHz
- Precision Reference (2%)
- Continuous Load Current up to 0.85A ($V_{in} = 12$ to 24V, DIP-8 package, see Note for Step-Down Application)

SCHEMATIC DIAGRAM



(Bottom View)

PIN CONNECTIONS



(Top View)

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power supply voltage	V_{CC}	40	V_{DC}
Comparator input voltage range	V_{IR}	-0.3 to +40	V_{DC}
Switch collector voltage	$V_{C(Switch)}$	40	V_{DC}
Switch emitter voltage ($V_{Pin1}=40V$)	$V_{E(Switch)}$	40	V_{DC}
Switch collector-to-emitter voltage	$V_{CE(Switch)}$	40	V_{DC}
Driver collector voltage	$V_{C(Driver)}$	40	V_{DC}
Driver collector current (Note 1)	$I_{C(Driver)}$	100	mA
Switch current	I_{Sw}	1.5	A
Operating junction temperature	T_J	+150	$^{\circ}C$
Operating ambient temperature range	T_A	-40 to +85	$^{\circ}C$
Storage temperature range	T_{STG}	-65 to +150	$^{\circ}C$
ESD for 34063M3K		2500	V


ELECTRICAL CHARACTERISTICS ($V_{CC}=5.0V$, $T_A=T_{Low}$ to T_{High} , unless otherwise specified.)

Characteristics	Symbol	Min	Typ	Max	Unit
OSCILLATOR					
Frequency ($V_{Pin5}=0V$, $C_T=1.0nF$, $T_A=25^\circ C$)	f_{osc}	24	33	42	kHz
Charge current ($V_{CC}=5.0V$ to $40V$, $T_A=25^\circ C$)	I_{chg}	24	35	42	μA
Discharge current ($V_{CC}=5.0V$ to $40V$, $T_A=25^\circ C$)	I_{dischg}	140	220	260	μA
Discharge-to-charge current ratio (Pin7 to V_{CC} , $T_A=25^\circ C$)	I_{dischg}/I_{chg}	5.2	6.5	7.5	-
Current limit sense voltage ($I_{chg}=I_{dischg}$, $T_A=25^\circ C$)	$V_{Ipk(sense)}$	250	300	350	mV
OUTPUT SWITCH (Note 2)					
Saturation voltage, Darlington connection $I_{Sw}=1.0A$, Pins1, 8 connected	$V_{CE(sat)}$	-	1.0	1.3	V
Saturation voltage, Darlington connection ($I_{Sw}=1.0A$, $R_{Pin8}=82\Omega$ to V_{CC} , Forced $\beta =20$)	$V_{CE(sat)}$	-	0.45	0.7	V
DC current gain ($I_{Sw}=1.0A$, $V_{CE}=5.0$, $T_A=25^\circ C$)	h_{FE}	50	75	-	-
Collector off-state current ($V_{CE}=40V$)	$I_{C(off)}$	-	40	100	μA
COMPARATOR					
Threshold voltage	V_{th}	1.225 1.21	1.25 -	1.275 1.29	V
Threshold voltage line regulation ($V_{CC}=3.0V$ to $40V$)	Reg_{line}	-	1.4	5.0	mV
Input bias current ($V_{in}=0V$)	I_{IB}	-	-20	-400	nA
TOTAL DEVICE					
Supply current ($V_{CC}=5.0V$ to $40V$, $C_T=1.0nF$, Pin7= V_{CC} , $V_{Pin5}>V_{th}$, Pin2 =Gnd, remaining pins - open)	I_{CC}	-	-	4.0	mA

NOTES:

1. Maximum package power dissipation limits must be observed.
2. Low duty cycle pulse techniques are used during the test to maintain junction temperature as close to ambient temperature as possible.



TYPICAL PERFORMANCE CHARACTERISTICS

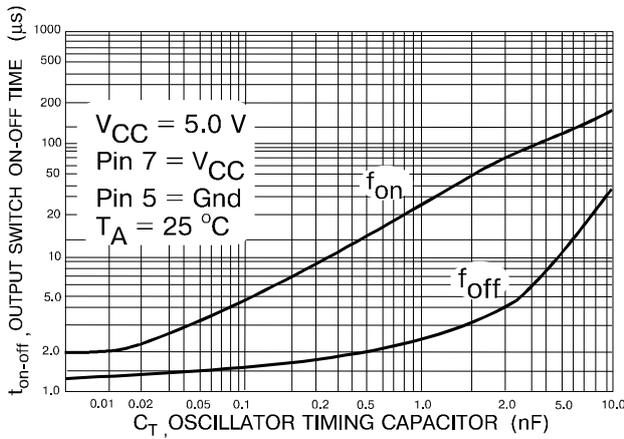


Fig.1. Output Switch on-off time versus Oscillator timing capacitor

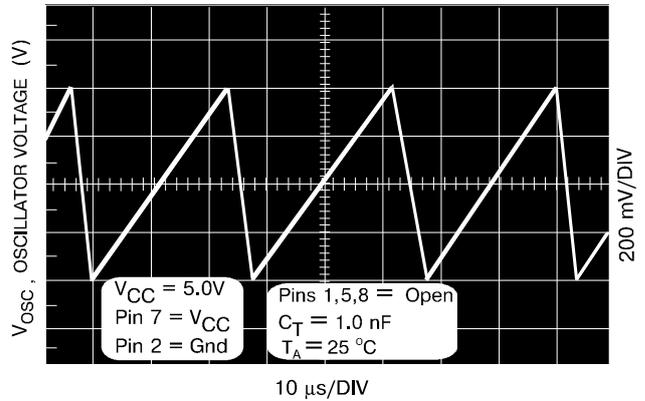


Fig.2. Timing capacitor waveform

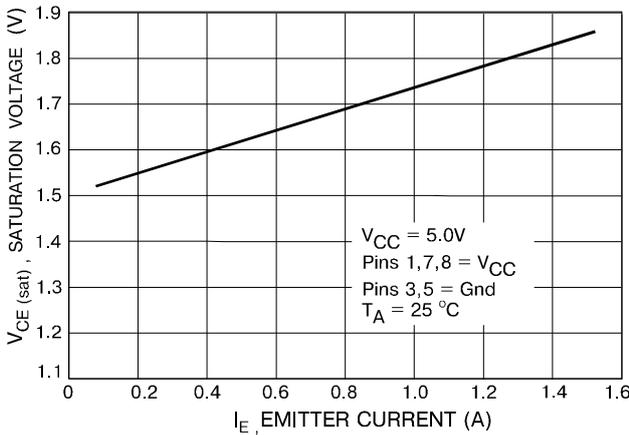


Fig.3. Emitter follower configuration output saturation voltage versus Emitter current

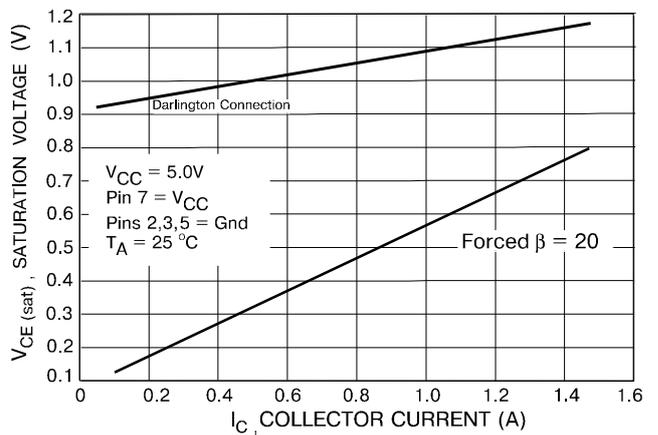


Fig.4. Common emitter configuration output saturation voltage versus Collector current

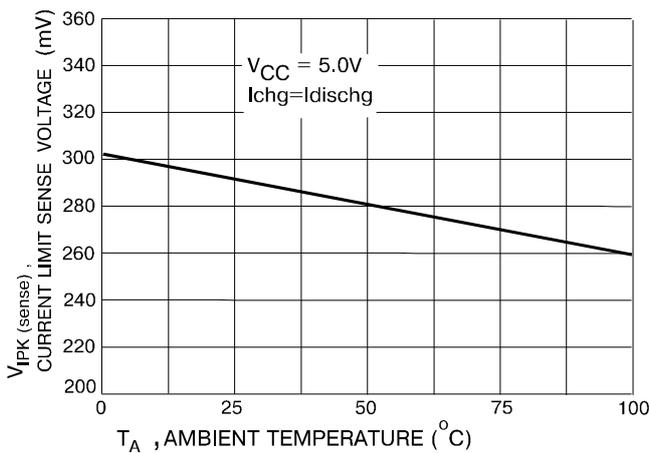


Fig.5. Current limit sense voltage versus Temperature

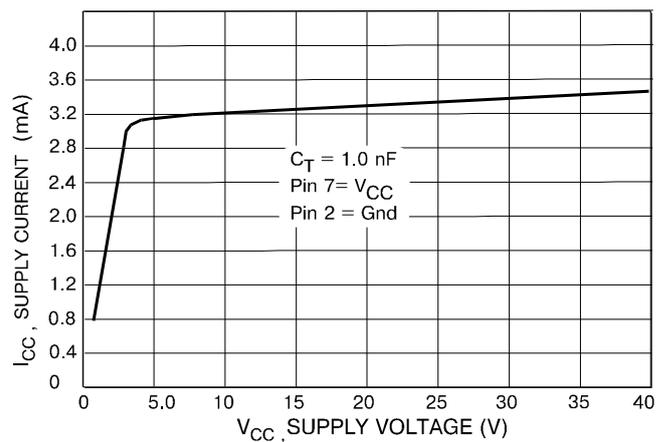


Fig.6. Standby supply current versus Supply voltage



APPLICATION INFORMATION

Fig.1. Step-up converter

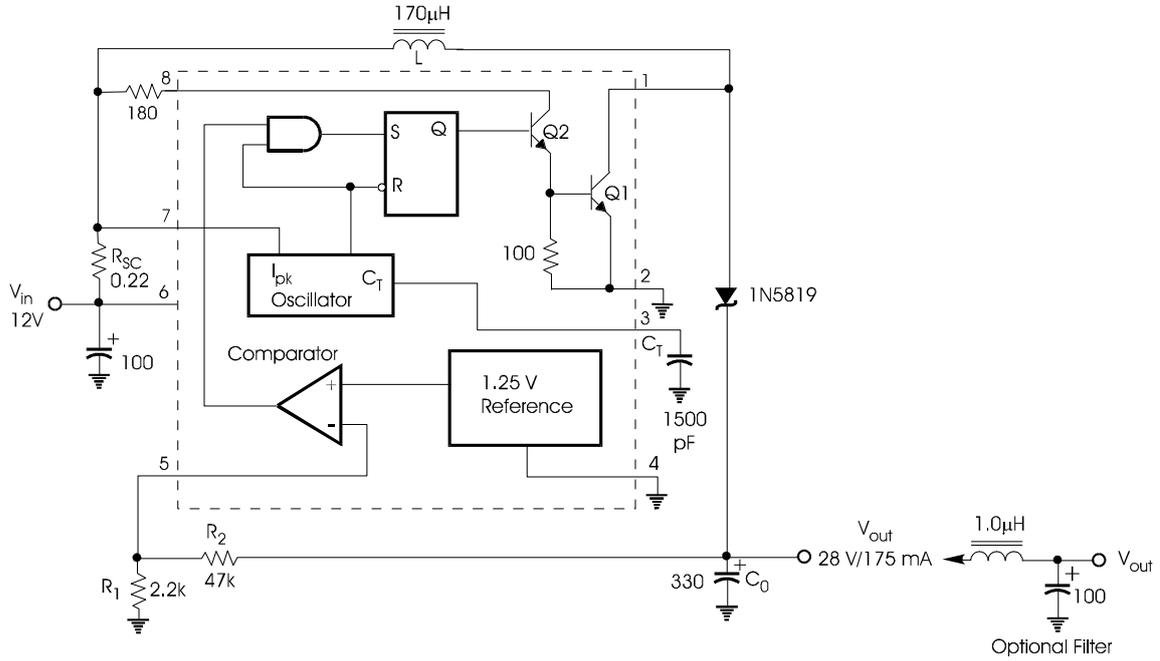
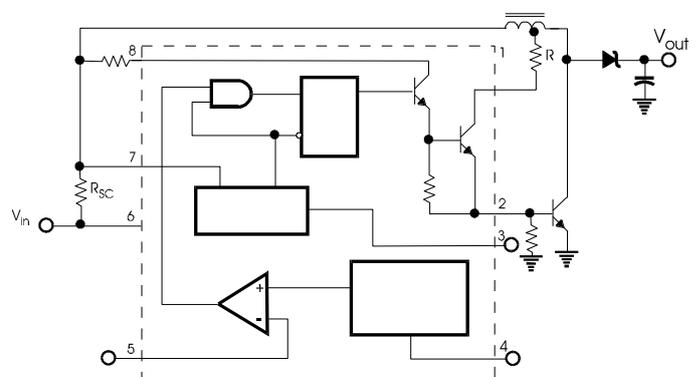
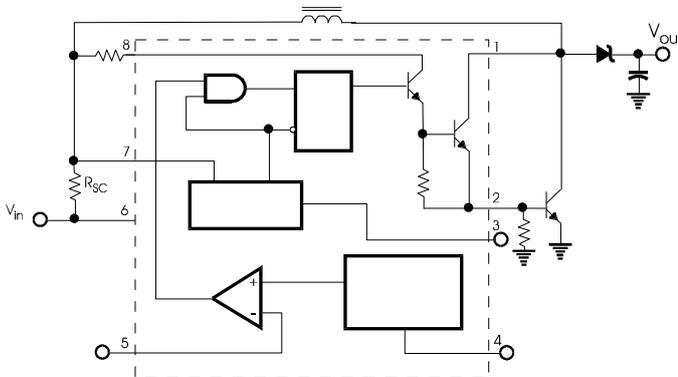


Fig.2. External current boost connections for $I_{C\ Peak}$ greater than 1.5A

2a. External NPN switch

2b. External NPN saturated switch



Note: R to 0 for constant V_{IN}

Fig.5. Voltage inverting converter

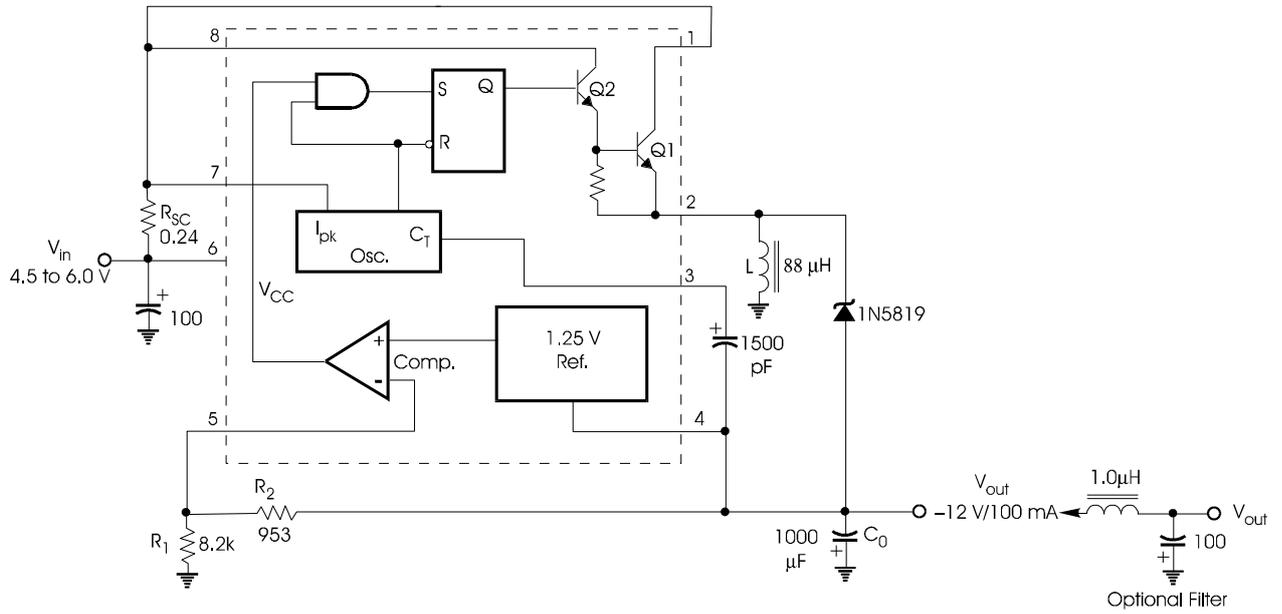
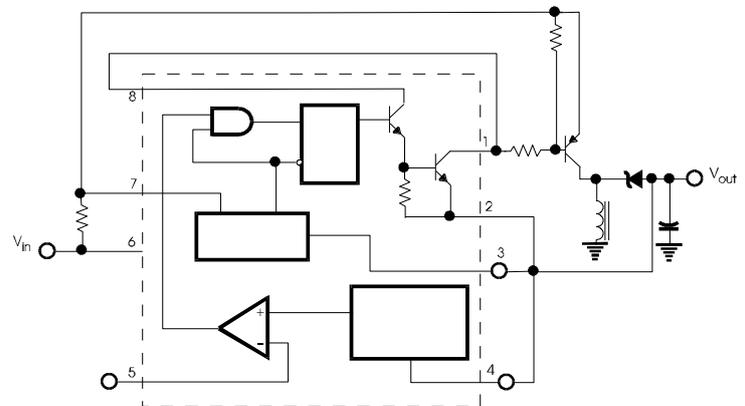
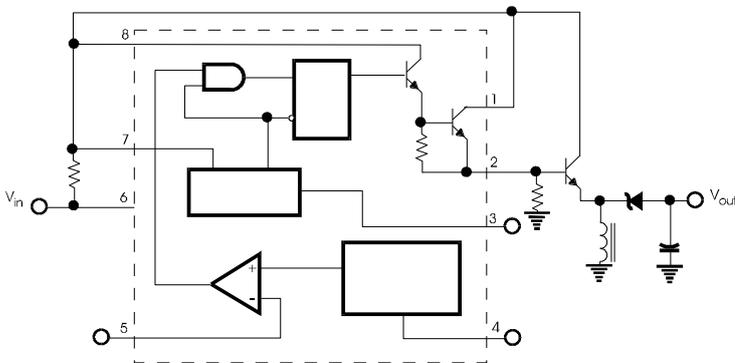


Fig.6. External current boost connections for $I_{C\ Peak}$ greater than 1.5A

6a. External NPN switch

6b. External PNP saturated switch





TABLE

DESIGN FORMULA

Calculation	Step-up	Step-down	Voltage-inverting
t_{on}	$\frac{V_{out} + V_F - V_{in(min)}}{V_{in(min)} - V_{sat}}$	$\frac{V_{out} + V_F}{V_{in(min)} - V_{sat} - V_{out}}$	$\frac{ V_{out} + V_F}{V_{in} + V_{sat}}$
$(t_{on} + t_{off})_{max}$	$\frac{1}{f_{min}}$	$\frac{1}{f_{min}}$	$\frac{1}{f_{min}}$
C_T	$4.0 \times 10^{-5} t_{on}$	$4.0 \times 10^{-5} t_{on}$	$4.0 \times 10^{-5} t_{on}$
$I_{pk(switch)}$	$2I_{out(max)} \left(\frac{t_{on}}{t_{off}} + 1 \right)$	$2I_{out(max)}$	$2I_{out(max)} \left(\frac{t_{on}}{t_{off}} + 1 \right)$
R_{sc}	$0.3/I_{pk(Switch)}$	$0.3/I_{pk(Switch)}$	$0.3/I_{pk(Switch)}$
$L_{(min)}$	$\left(\frac{V_{in(min)} - V_{sat}}{I_{pk(switch)}} \right) \times t_{on(max)}$	$\left(\frac{V_{in(min)} - V_{sat} - V_{out}}{I_{pk(switch)}} \right) \times t_{on(max)}$	$\left(\frac{V_{in(min)} - V_{sat}}{I_{pk(switch)}} \right) \times t_{on(max)}$
C_o	$9 \frac{I_{out} t_{on}}{V_{ripple(pp)}}$	$\frac{I_{pk(switch)} (t_{on} + t_{off})}{8V_{ripple(pp)}}$	$9 \frac{I_{out} t_{on}}{V_{ripple(pp)}}$

TERMS AND DEFINITIONS

V_{sat} – Saturation voltage of the output switch.

V_f – Forward voltage drop of the output rectifier.

The following power supply characteristics must be chosen:

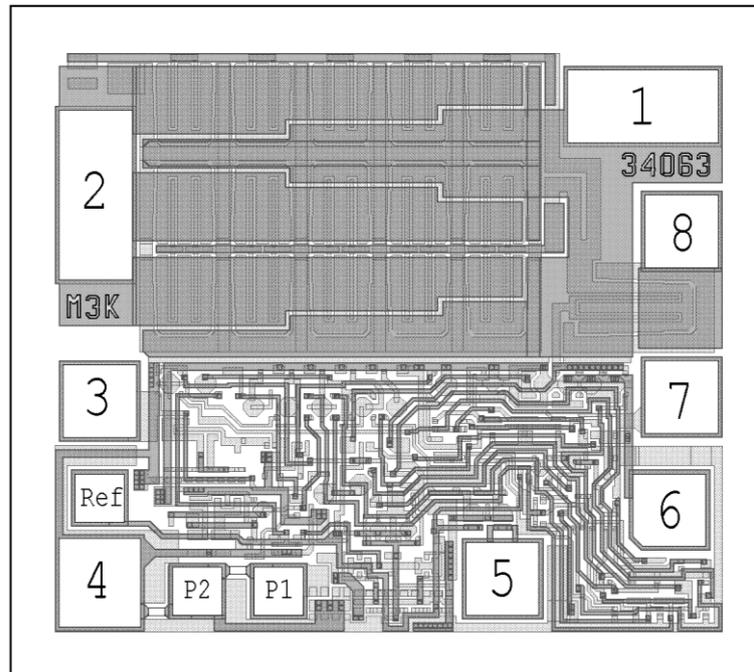
V_{in} – Nominal input voltage.

V_{out} – Desired output voltage, $|V_{out}| = 1.25 \left(1 + \frac{R_2}{R_1} \right)$

f_{min} – Minimum desired output switching frequency at the selected values of V_{in} and I_{out} .

$V_{ripple(p-p)}$ – Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

34063M3K Pad location



Pads ²	Package pin	Pin name	Description	Center coordinates		Pad size	
				X	Y	W	H
1 (see Note)	1	SC	Switch collector	777	705	185	90
2 (see Note)	2	SE	Switch emitter	105	595	90	210
3	3	C _T	Timing capacitor	110	340	90	90
4	4	Gnd	Ground	112	115	100	110
5	5	CII	Comparator inverting input	605	120	90	90
6	6	V _{CC}	Supply voltage	810	205	90	90
7	7	I _{pk sense}	I _{pk} sense	825	345	90	90
8	8	DRVCOL	Driver collector	825	550	90	90
Additional pads							
P1	-	-	Ref trimming	330	105	60	60
P2	-	-	Ref trimming	230	105	60	60
Ref	-	-	Ref checking	110	220	60	60

Note: 1. Two bonding wires should be connected to Pads 1 and 2 (each).



Assembly Characteristics

No.	Assembly Characteristics	Value
1	Wafer Size	6 Inch
2	Wafer Thickness before Grinding	675 +/-25 μm
3	Scribe Street Width	80 μm
4	Chip Size (including Scribe Line)	0.93 \times 0.83 mm ²
5	Die Attach Material	Substrate is connected to GND
6	Quantity of Bond Pad Metal Layers	2
7	Pad Thickness	2.25 μm
8	Composition of Metal Layers	Al+Si(1.0%)+Ti(0.5%)
9	Min. Bond Pad Opening Size	90 \times 90 μm
10	Min. Bond Pad Pitch	140 μm
11	Min. Wire Diameters	1 mil (25.4 μm)
12	Circuit Under Pad Design (CUP)	No

For your information

Pb-free products:

- ◆ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.

Green products:

- ◆ Lead-free (RoHS compliant)
- ◆ Halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

The appearance complies with the requirements of the company standards.